



## Schottky Diodes



### Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness : Tin plated leads, solderable per 002 and JESD22-B102

**Polarity:** As marked

### Maximum Ratings (T<sub>a</sub>=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Device marking code			MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Repetitive Peak Reverse Voltage	VRRM	V	80	100	120	150	200
Average Rectified Output Current @60Hz sine wave, R-load, T <sub>a</sub> =25	I <sub>O</sub>	A	10				
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T <sub>a</sub> =25	I <sub>FSM</sub>	A	100				
Current Squared Time @1ms t 8.3ms T <sub>j</sub> =25	I <sup>2</sup> t	A <sup>2</sup> s	41				
Storage Temperature	T <sub>stg</sub>						

				MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Maximum instantaneous forward voltage drop per diode	V <sub>FM</sub>	V	I <sub>FM</sub> =5.0A	0.85		0.9		0.95
Maximum DC reverse current at rated DC blocking voltage per diode	I <sub>RRM1</sub>	mA	V <sub>RM</sub> =V <sub>RRM</sub> T <sub>a</sub> =25	0.1				
	I <sub>RRM2</sub>		V <sub>RM</sub> =V <sub>RRM</sub> T <sub>a</sub> =100	20				

Note1:Pulse test:300uS pulse width,1% duty cycle

Note2:Pulse test:pulse width 40mS



## MBR1080CT THRU MBR10200CT

### Thermal Characteristics (T<sub>a</sub>=25 Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Thermal Resistance	Between junction and case	R <sub>J-C</sub>	W	2.0				

### Ordering Information (Example)





**Outline Dio**